

ABSTRACT

In a method for producing a bonding wafer by the hydrogen ion delamination method comprising at least a step of bonding a base wafer and a bond wafer having a micro bubble layer formed by gas ion implantation and a step of delaminating them at the micro bubble layer as a border, a peripheral portion of a thin film formed on the base wafer is removed after the delamination step. Preferably, a region of 1-5 mm from the peripheral end of the base wafer is removed. In the production of a bonding wafer by the hydrogen ion delamination method, there can be provided a bonding wafer free from problems such as generation of particles from peripheral portion of the wafer and generation of cracks in the SOI layer.